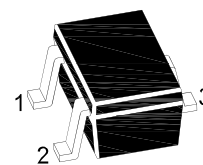


NPN Silicon Epitaxial Planar Transistor



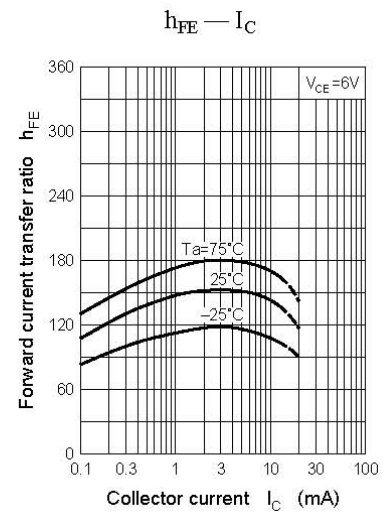
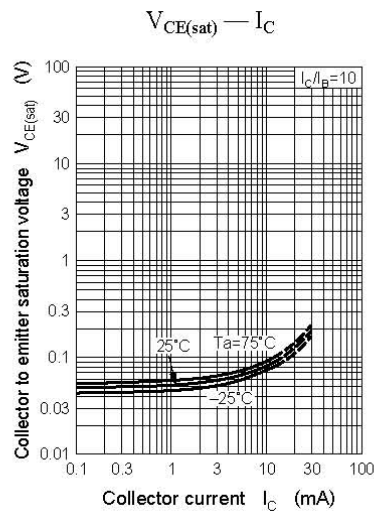
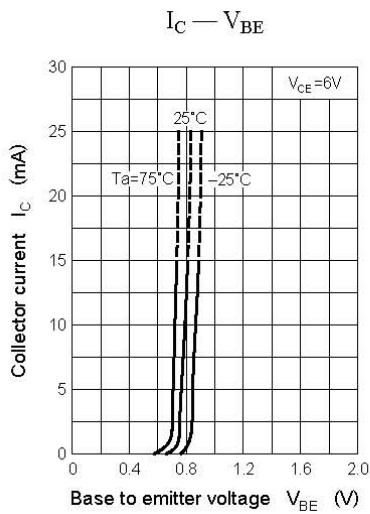
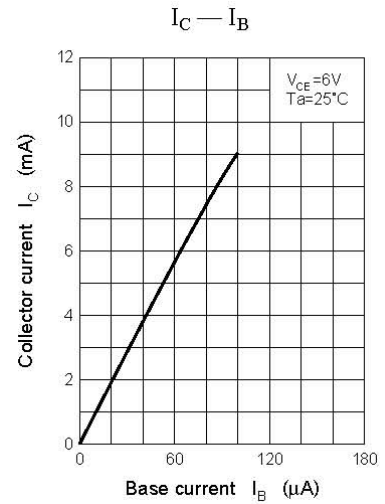
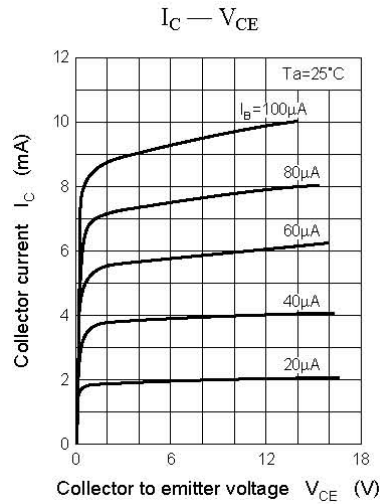
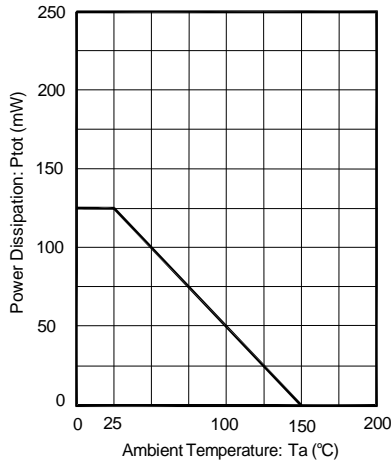
1.Base 2.Emitter 3.Collector
SOT-523 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	3	V
Collector Current	I_C	15	mA
Power Dissipation	P_{tot}	125	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain at $V_{CE} = 6\text{ V}$, $I_C = 1\text{ mA}$	Current Gain Group B	h_{FE}	40	110	-
	C	h_{FE}	65	160	-
	D	h_{FE}	100	260	-
Collector Base Cutoff Current at $V_{CB} = 12\text{ V}$	I_{CBO}	-	50	nA	
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{BR(CBO)}$	30	-	V	
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	20	-	V	
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{BR(EBO)}$	3	-	V	
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$	$V_{CE(sat)}$	-	0.5	V	
Transition Frequency at $V_{CE} = 6\text{ V}$, $I_C = 1\text{ mA}$, $f = 200\text{ MHz}$	f_T	450	-	MHz	
Collector Base Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	1.7	pF	





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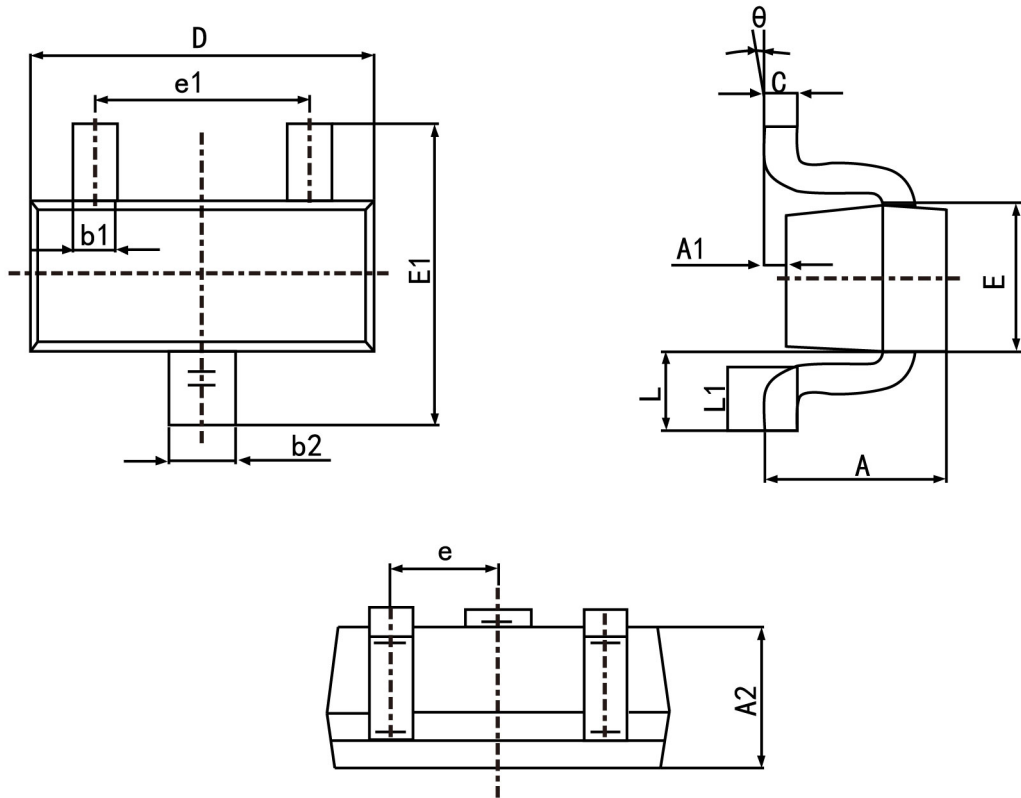
MMBTSC4627E

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
c	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500	TYP.
e1	0.900	1.100
L	0.400 REF.	
L1	0.260	0.460
θ	0°	8°